T8: Electrodeposition Processes in Semiconductor Device Fabrication

To Use this Index: Scroll down or use the bookmarks in the left-hand frame to move to a new location in this index. Click on a blue paper title to view that paper. To return to this index after viewing a paper, click the PREVIOUS MENU bookmark in the left frame.

Session 91 - Recent Advances in Chemical Mechanical Planarization I Chair: SV Babu

- 91c Tribological, Thermal and Kinetic Attributes of Copper and Silicon Dioxide CMP Processes Y. Zhuang, Z. Li, J. Sorooshian and A. Philipossian and L. Borucki
- 91d Theoretical and Experimental Investigation of ILD Removal Rates, Coefficient of Friction, and Pad Flattening Ratio Len Borucki, H. Lee, Y. Zhuang and A. Philipossian

Session 92 - Recent Advances in Chemical Mechanical Planarization II

Chair: Ara Philipossian

92c Evaluation of High Pressure Micro Jet Technology as an Alternative Pad Conditioning Method for Silicon Dioxide Chemical Mechanical Planarization Hyo-Sang Lee, Masano Sugiyama, Ara Philipossian, Yoshiyuki Seike, Mineo Takaoka, Keiji Miyachi

Session 93 - Electropolishing and Chemical Mechanical Polishing (CMP)

Chair: Robert Opila Vice Chair: Uzi Landau

- 93c Electrochemical Polishing of Patterned Copper Films J. Huo, R. Solanki and J. McAndrew
- 93e Surface Texture Measurements of CMP Pads Using a Flow-Based Characterization Test Ravi Palaparthi and Gregory P. Muldowney